A 300 nW, 15 ppm/°C, 20 ppm/V CMOS Voltage Reference Circuit Consisting of Subthreshold MOSFETs

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Abstract—A low-power CMOS voltage reference was developed using a 0.35 μm standard CMOS process technology. The device consists of MOSFET circuits operated in the subthreshold region and uses no resistors. It generates two voltages having opposite temperature coefficients and adds them to produce an output voltage with a near-zero temperature coefficient. The resulting voltage is equal to the extrapolated threshold voltage of a MOSFET at absolute zero temperature, which was about 745 mV for the MOSFETs we used. The temperature coefficient of the voltage was 7 ppm/°C at best and 15 ppm/°C on average, in a range from −20 to 80°C. The line sensitivity was 20 ppm/V in a supply voltage range of 1.4–3 V, and the power supply rejection ratio (PSRR) was −45 dB at 100 Hz. The power dissipation was 0.3 μW at 80°C. The chip area was 0.05 mm². Our device would be suitable for use in subthreshold-operated, power-aware LSIs.

Index Terms—CMOS, voltage reference, ultra-low power, subthreshold, weak inversion, process variation, die-to-die variation, power-aware LSIs.

I. INTRODUCTION

One of the promising areas of research in microelectronics is the development of ultra-low power LSIs that operate in the subthreshold region of MOSFETs, i.e., a region at which the gate-source voltage of MOSFETs is lower than the threshold voltage [1], [2]. Such LSIs would be suitable for use in power-aware LSI applications such as portable mobile devices, implantable medical devices, and smart sensor networks [3]. These devices have to operate with ultra-low power, e.g., a few microwatts or less [3]–[5] because they will probably be placed under conditions where they have to get the necessary energy from poor energy sources such as microbatteries and environmental energy sources [6]. As a step toward such LSIs, we first need to develop a voltage reference circuit that can operate with an ultra-low current, several tens of nanoamperes or less. To achieve such low power operation, the circuit has to be operated in the subthreshold region of MOSFET.

A voltage reference is one of the important building blocks for analog, digital, and mixed-signal circuit systems in microelectronics. It generates a constant reference voltage for other various components such as operational amplifiers, comparators, and AD/DA converters. For this purpose, bandgap reference circuits with CMOS-based vertical bipolar transistors are conventionally used in CMOS LSIs [7], [8]. However, they need resistors with a high resistance of several hundred megaohms to achieve low-current, subthreshold operation. Such a high resistance needs a large area to be implemented, and this makes conventional bandgap references unsuitable for use in ultra-low power LSIs. Therefore, modified voltage reference circuits for low-power LSIs have been reported (see [9]–[13]). However, these circuits have various problems. For example, their power dissipations are still large, and their outputs voltages are sensitive to supply voltage and temperature variations; these are quite inconvenient for practical use in ultra-low power LSIs. Moreover, the effect of the process variations on the reference voltage was not discussed in detail.

To solve these problems, we developed a new voltage reference that can operate with sub-microwatt power dissipation and has less temperature sensitivity and a smaller line sensitivity [14] than the reported works [9]–[13]. Our device consists of subthreshold MOSFET circuits and uses no resistors. It generates two voltages having opposite temperature coefficients (TCs), i.e., a MOSFET threshold voltage with a negative TC and a multiple of the thermal voltage with a positive TC, and adds them to produce an output voltage with a zero TC. The output voltage is equal to the threshold voltage of a MOSFET at 0 K and is about 745 mV for MOSFETs we used. The voltage is quite insensitive to temperature and the supply voltage variations, although its value fluctuates with process variation. By utilizing the nature of the reference voltage, which changes with the process conditions of threshold voltage in each LSI chip, the circuit can be used as an elementary circuit block for on-chip process compensation systems. The following sections provide the details on our device. Section II describes the principle of our voltage reference and discusses the effect of process variations. Section III explains the method of designing the circuit with a SPICE simulator. Section IV shows the characteristics of a prototype device we made using a 0.35 μm standard CMOS process technology. A small TC of 7 ppm/°C and a line sensitivity of 20 ppm/V were achieved.

II. CIRCUIT CONFIGURATION

The principle of our voltage reference circuit is illustrated in Fig. 1. The circuit consists of a current source subcircuit...
and a bias-voltage subcircuit. The current source subcircuit is a modified \( \beta \) multiplier self-biasing circuit that uses a MOS resistor \( R_{M1} \) instead of ordinary resistors. It generates a current, \( I_P \). The bias-voltage subcircuit accepts current \( I_P \) through pMOS current mirrors and produces an output voltage (i.e., reference voltage), \( V_{\text{REF}} \). The bias-voltage subcircuit consists of a transistor (\( M_1 \)) and two source-coupled pairs (\( M_3-M_6 \) and \( M_5-M_7 \)). The gate-source voltages of \( M_3-M_7 \) in the bias-voltage subcircuit and \( M_{R1} \) in the current source subcircuit form a closed loop [15], [16]. All the MOSFETs except for \( M_{R1} \) are operated in the subthreshold region. The MOS transistor \( M_{R1} \) is operated in a strong-inversion, deep-triode region. The circuit generates two voltages with a negative TC and a positive TC and combines them to produce a constant voltage with a zero TC. The following sections describe the operation in detail.

### A. Operation Principle

The subthreshold drain current \( I_D \) of a MOSFET is an exponential function of the gate-source voltage \( V_{GS} \) and the drain-source voltage \( V_{DS} \), and given by

\[
I_D = K I_0 \exp \left( \frac{V_{GS} - V_{TH}}{\eta V_T} \right) \times \left( 1 - \exp \left( -\frac{V_{DS}}{V_T} \right) \right),
\]

(1)

where \( K \) is the aspect ratio \((= W/L)\) of the transistor, \( \mu \) is the carrier mobility, \( C_{OX} \) is the gate-oxide capacitance, \( V_T \) is the thermal voltage, \( k_B \) is the Boltzmann constant, \( T \) is the absolute temperature, and \( q \) is the elementary charge, \( V_{TH} \) is the threshold voltage of a MOSFET, and \( \eta \) is the subthreshold slope factor [1], [17]. For \( V_{DS} > 0.1 \text{ V} \), current \( I_D \) is almost independent of \( V_{DS} \) and given by

\[
I_D = K I_0 \exp \left( \frac{V_{GS} - V_{TH}}{\eta V_T} \right).
\]

(2)

In the current-source subcircuit, gate-source voltage \( V_{GS1} \) in \( M_1 \) is equal to the sum of gate-source voltage \( V_{GS2} \) in \( M_2 \) and drain-source voltage \( V_{DSR1} \) in \( M_{R1} \), i.e.,

\[
V_{GS1} = V_{GS2} + V_{DSR1}.
\]

(3)

Because currents \( I_P \) in \( M_1 \) and in \( M_2 \) are equal to each other, (3) can be rewritten as

\[
V_{DSR1} = \eta V_T \ln \left( \frac{K_2}{K_1} \right).
\]

(4)

MOS resistor \( M_{R1} \) is operated in a strong-inversion, deep-triode region, so its resistance \( R_{M1} \) is given by

\[
R_{M1} = \frac{1}{K_{R1} \mu C_{OX} (V_{\text{REF}} - V_{TH})}.
\]

(5)

From (3), (4), and (5), we arrive at the expression

\[
I_P = \frac{V_{DSR1}}{R_{M1}} = \frac{1}{K_{R1} \mu C_{OX} (V_{\text{REF}} - V_{TH})} \eta V_T \ln \left( \frac{K_2}{K_1} \right).
\]

(6)

for current \( I_P \). In the bias-voltage subcircuit, the gate-source voltages \( V_{GS3} \) through \( V_{GS7} \) of the transistors form a closed loop, and the currents in \( M_4 \) and \( M_6 \) are \( 3I_P \) and \( 2I_P \). Therefore, we find that output voltage \( V_{\text{REF}} \) of the circuit is given by

\[
V_{\text{REF}} = V_{GS4} - V_{GS3} + V_{GS5} - V_{GS5} + V_{GS7} = V_{GS4} + \eta V_T \ln \left( \frac{2K_3 K_5}{K_6 K_7} \right)
\]

\[
= V_{TH} + \eta V_T \ln \left( \frac{3I_P}{K_4 K_5} \right) + \eta V_T \ln \left( \frac{2K_3 K_5}{K_6 K_7} \right)
\]

(7)

where we assumed that the mismatch between the threshold voltages of the transistors can be ignored. Equation (7) shows that \( V_{\text{REF}} \) can be expressed as a sum of the gate-source voltage \( V_{GS4} \) and thermal voltage \( V_T \) scaled by the transistor sizes. Because \( V_{TH} \) has a negative TC and \( V_T \) has a positive TC, output voltage \( V_{\text{REF}} \) with a zero TC can be obtained by adjusting the size of the transistors.

The temperature dependence of the threshold voltage can be given by

\[
V_{TH} = V_{TH0} - \kappa T
\]

(8)

where \( V_{TH0} \) is the threshold voltage at 0 K, and \( \kappa \) is the TC of \( V_{TH} \) [18]. Equations (6) and (8) show that output voltage \( V_{\text{REF}} \) can be rewritten as

\[
V_{\text{REF}} = V_{TH0} - \kappa T + \eta V_T \ln \left\{ 6 \eta K_{R1} K_3 K_5 (V_{\text{REF}} - V_{TH}) \ln \left( \frac{K_2}{K_1} \right) \right\}.
\]

(9)

The TC of \( V_{\text{REF}} \) is given by

\[
\frac{dV_{\text{REF}}}{dT} = -\kappa + \frac{\eta k_B}{q} \ln \left\{ \frac{6 \eta K_{R1} K_3 K_5 (V_{\text{REF}} - V_{TH}) \ln \left( \frac{K_2}{K_1} \right)}{K_4 K_6 K_7 (\eta - 1) V_T} \right\}
\]

\[
+ \eta V_T \left\{ \frac{1}{V_{\text{REF}} - V_{TH}} \frac{dV_{\text{REF}}}{dT} + \kappa \right\}.
\]

(10)
On condition that $V_{\text{REF}} - V_{\text{TH,0}} \ll kT$ and $\eta V_T \ll kT$, the TC of $V_{\text{REF}}$ can be rewritten as

$$
\frac{dV_{\text{REF}}}{dT} = -\frac{k}{q} + \frac{\eta k_B}{q} \ln \left( \frac{g_{\text{eq}} K_{\text{RI}1} K_{\text{RI}2} K_2}{k_B (\eta - 1)} \frac{K_{\text{RI}2} K_2 K_3}{K_{\text{RI}1} K_{\text{RI}2} K_4 K_6 K_7} \right) \ln \left( \frac{K_2}{K_1} \right) \tag{11}
$$

(see the Appendix for the derivation of (11)). Therefore, a zero TC can be achieved on condition that

$$
-\frac{k}{q} + \frac{\eta k_B}{q} \ln \left( \frac{g_{\text{eq}} K_{\text{RI}1} K_{\text{RI}2} K_2}{k_B (\eta - 1)} \frac{K_{\text{RI}2} K_2 K_3}{K_{\text{RI}1} K_{\text{RI}2} K_4 K_6 K_7} \right) = 0, \tag{12}
$$

A zero TC voltage can be obtained by setting the aspect ratios $K_i$ in accordance with (12). From (9) and (12), we find that

$$
V_{\text{REF}} = V_{\text{TH,0}}. \tag{13}
$$

This shows that the circuit generates a voltage equal to the threshold voltage of MOSFETs at 0 K.

Using (6), (8), and (9), we can express current $I_P$ as

$$
I_P = K_{\text{RI}1} \mu C_{\text{OX}} K_T \eta V_T \ln \left( \frac{K_2}{K_1} \right). \tag{14}
$$

The current is determined only by the aspect ratios ($K_1$, $K_2$, and $K_{\text{RI}1}$) and the temperature coefficient ($\kappa$) of the threshold voltage of MOSFETs, and it is independent of $V_{\text{TH,0}}$. The dependence of $\kappa$ on process variation is far smaller than that of $V_{\text{TH,0}}$ as shown in the next section, so current $I_P$ is less dependent on process variations.

The TC of $I_P$ is given by

$$
\frac{1}{I_P} \frac{\partial I_P}{\partial T} = \mu \frac{\partial T}{\partial T} + \frac{1}{V_T} \frac{\partial V_T}{\partial T}. \tag{15}
$$

The temperature dependence of the mobility can be expressed as

$$
\mu = \mu_0 \left( \frac{T}{T_0} \right)^{-m} \tag{16}
$$

where $\mu_0$ is the mobility at temperature $T_0$, and $m$ is the mobility temperature exponent [18]. Equations (15) and (16) show that the TC of the current can be given by

$$
1 \frac{\partial I_P}{\partial T} = \frac{2 - m}{T}. \tag{17}
$$

The value of $m$ is about 1.5 in standard CMOS process technologies, so current $I_P$ has a positive TC and increases with temperature.

### B. Dependence of Output Voltage on Temperature and Process Variation

The output voltage $V_{\text{REF}}$ of our circuit is equal to the threshold voltage of MOSFETs at 0 K, so its value depends on process variation. However, its TC is quite insensitive to process variation and is very small in a wide temperature range. These are discussed in the following.

Process variations can be classified into two categories: i.e., within-die (WID) (intra-die) variation and die-to-die (D2D) (inter-die) variation [19]–[21]. The WID variation causes mismatches between transistor parameters within a chip and affects the relative accuracy of the parameters. It can be reduced by using large-sized transistors and various analog layout techniques [21], [22]. In our circuit design, we used a large $W/L$ values and a common centroid technique. In contrast, the D2D variation affects the absolute accuracy of transistor parameters and is difficult to reduce with existing techniques. Our circuit generates voltage $V_{\text{REF}}$ equal to the threshold voltage of a MOSFET at 0 K, so the D2D variation will directly affect $V_{\text{REF}}$. On the other hand, the TC of $V_{\text{REF}}$ is quite insensitive to process variations and is very small in a wide temperature range. We show these characteristics with the aid of computer simulation.

The TC of the reference voltage is expressed by (11) and can be set to 0 if (12) is satisfied. Therefore $\kappa$ (TC of the threshold voltage of MOSFETs) is the key parameter to achieve zero TC operation. The threshold voltage in (8) is theoretically given by

$$
V_{\text{TH}} = \frac{E_g}{2q} + \psi_B + \frac{\sqrt{4\varepsilon_s q N_A V_{\text{TH}}}}{C_{\text{OX}}}, \tag{18}
$$

$$
\psi_B = V_T \ln \left( \frac{N_A}{n_i} \right),
$$

where $\psi_B$ is the difference between Fermi-level potential and intrinsic-level potential, $\varepsilon_s$ is the silicon permittivity, $N_A$ is the channel doping concentration, $n_i$ is the intrinsic carrier density, and $E_g$ is the bandgap energy of silicon [17]. Equation (18) shows that the TC, $(\kappa = dV_{\text{TH}}/dT)$, of the threshold voltage is given by

$$
\kappa = \frac{-(2\eta - 1) k_B}{q} \ln \left( \frac{\sqrt{N_C N_V}}{N_A} \right) + \frac{3}{2} + \eta - \frac{1}{q} \frac{dE_g}{dT}. \tag{19}
$$

where $N_C$ and $N_V$ are the effective densities of states in the conduction and valence bands [17]. From (18) and (19), we find that both $V_{\text{TH}}$ and its temperature coefficient $\kappa$ depend on channel
doping concentration $N_A$. This concentration is a process-dependent quantity, so $K$ can change with process variation. The change is very small, however, because $K$ is a logarithmic function of $N_A$. Therefore, the TC of $V_{TH}$ has little dependence on process variation.

To study the effect of process variation on the threshold voltage and its TC, we calculated (18) and (19) numerically using a set of 0.35 $\mu$m CMOS parameters at room temperature. Fig. 2 shows the result, a plot of the calculated $V_{TH}$ and $K$ as a function of $N_A$. The dashed lines (2.0–3.3 × 10^{17} cm^{-3}) represent the range of $N_A$ for the CMOS process we used. In this concentration range, threshold voltage $V_{TH}$ changes by ±20% with $N_A$, while its temperature coefficient $K$ changes by only ±2%. Therefore, the TC of the output voltage hardly depends on process variation.

C. Entire Configuration for Actual Circuit

The entire circuit we designed is illustrated in Fig. 3. Capacitors $C_{C1}, C_{C2}$, and $C_{C3}$ are used to prevent parasitic oscillation and noise disturbances. A differential amplifier $M_{10}$–$M_{14}$ and a current mirror $M_8$–$M_9$ are used to increase the power supply rejection ratio (PSRR) to reduce the line sensitivity of the circuit. A start-up circuit $M_{15}$–$M_{19}$ is used to avoid the stable state in the zero bias condition. Table I shows the size of transistors $M_1$–$M_7$ and $M_{R1}$.

<table>
<thead>
<tr>
<th>TABLE I</th>
<th>Transistor Sizes of Our Circuit</th>
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<tr>
<td>$M_1$</td>
<td>60 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 20</td>
</tr>
<tr>
<td>$M_2$</td>
<td>300 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 100</td>
</tr>
<tr>
<td>$M_3$</td>
<td>252 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 84</td>
</tr>
<tr>
<td>$M_4$</td>
<td>6 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 2</td>
</tr>
<tr>
<td>$M_5$</td>
<td>252 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 84</td>
</tr>
<tr>
<td>$M_6$</td>
<td>6 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 2</td>
</tr>
<tr>
<td>$M_7$</td>
<td>6 $\mu$m / 3 $\mu$m = (3 $\mu$m / 3 $\mu$m) × 2</td>
</tr>
<tr>
<td>$M_{R1}$</td>
<td>4 $\mu$m / 150 $\mu$m = (2 $\mu$m / 150 $\mu$m) × 2</td>
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III. SIMULATION RESULTS

We confirmed the operation of our circuit with the aid of a SPICE simulation using a set of 0.35 $\mu$m standard CMOS parameters and assuming a 1.5 V power supply. To study the dependence of the output voltage on process variations, we performed Monte Carlo simulations assuming both D2D variation (e.g., $\Delta V_{TH}, \Delta T_{OX}, \Delta L$, $\Delta W$) and WID variation (e.g., $\sigma_{V_{TH}}, \sigma_{T_{OX}}, \sigma_{L}, \sigma_{W}$) in transistor parameters. For WID variation, we assumed that every parameter shows a Gaussian distribution that depends on device area (e.g., $\sigma_{V_{TH}} = A_{V_{TH}}/\sqrt{W}$) [19]–[21]. For D2D variation, we assumed a uniform distribution (e.g., $-0.1$ V $< \Delta V_{TH} < 0.1$ V), which shows worst-case corners independent of device area [19]–[21]. Let us call a Monte Carlo simulation for a set of parameters a “run”.

The results for 300 runs are depicted in Figs. 4 and 5. Fig. 4 shows the dispersion of $V_{REF}$ from the average value ($V_{REF}$) in the temperature range from −20 to 80°C as a function of D2D threshold-voltage variation $\Delta V_{TH}$. Each open circle shows $V_{REF}$ for a run. As discussed in Section II, $V_{REF}$ varies significantly with each run in a range from 0.7 V to 0.9 V; this reflects the variation in transistor parameters for each run. The value of $V_{REF}$ depends linearly on $\Delta V_{TH}$ because the circuit produces the voltage equal to the 0-K threshold voltage of MOSFETs. Fig. 5 shows the distribution of $V_{REF}$. The average of $V_{REF}$ was 840 mV, and the standard deviation was 60 mV. The coefficient of variation $\sigma/\mu$ was 7%, including D2D and WID variations.

IV. EXPERIMENTAL RESULTS

We fabricated a prototype chip, using a 0.35 $\mu$m, 2-poly, 4-metal standard CMOS process. Fig. 6 shows a micrograph of
Fig. 4. Average output voltage as a function of D2D variation $\Delta V_{TH}$ of threshold voltage, as obtained from Monte Carlo simulation of 300 runs. Output voltage shows a linear dependence on threshold voltage ($\Delta V_{REF}/\Delta V_{TH} \approx 1$).

Fig. 5. Distribution of output voltage, as obtained from Monte Carlo simulation of 300 runs.

our chip. The chip area was 0.055 mm$^2$ ($\approx$200 $\mu$m x 275 $\mu$m).

Fig. 6. Micrograph of chip. Chip area is 0.055 mm$^2$.

Fig. 7 shows measured output voltage $V_{REF}$ as a function of temperature, with supply voltage $V_{DD}$ as a parameter. Almost constant voltage was able to be achieved. The average of output voltage was 745 mV. The temperature variation was 0.48 mV in a temperature range from $-20$ to $80^\circ$C, so the temperature coefficient was 7 ppm/$^\circ$C.

Fig. 8 shows output voltage $V_{REF}$ at room temperature as a function of supply voltage. The circuit operated correctly when supply voltage was higher than 1.4 V. The line sensitivity was 20 ppm/V in the power range of 1.4 to 3 V. Fig. 9 shows the power supply rejection ratio (PSRR) at room temperature with a 1 pF filtering capacitor and a 2 V power supply. The PSRR was $-45$ dB at 100 Hz. Thus, we were able to achieve the voltage reference circuit that was almost independent of temperature and supply voltage.

Fig. 10 shows measured current $I_P$ as a function of temperature, with power supply voltage as a parameter. The current $I_P$ was about 36 nA at room temperature and reached the maximum of 39 nA at $80^\circ$C. The power dissipation of the circuit with a 1.5 V power supply was 0.32 $\mu$W at room temperature and varied from 0.28 to 0.35 $\mu$W at temperatures from $-20$ to $80^\circ$C. The temperature variation of the power dissipation was 0.2%/$^\circ$C.

To study the D2D variation of our device, we measured 17 samples, each on a different chip, and confirmed their constant-voltage operation. Fig. 11 shows measured output voltage $V_{REF}$ as a function of temperature for a 1.5 V supply voltage. The D2D
variation in $V_{\text{REF}}$ was 25 mV. This value was far smaller than expected from the Monte Carlo simulation. This is so because the sample chips were fabricated from the same wafer, the variation of the reference voltage became smaller, and in our simulations, we assumed a uniform distribution for the D2D variation. This seems, however, to be an overestimation on the D2D variation, and in practice, a broad Gaussian distribution would be more suitable to represent the D2D variation.

Temperature coefficients from 7 to 45 ppm/°C were observed in the 17 samples. The average TC of $V_{\text{REF}}$ was 15 ppm/°C. Fig. 12 shows the distribution of output voltage $V_{\text{REF}}$ at room temperature. The coefficient of variation $\sigma/\mu$ was 0.87%.

Table II summarizes the characteristics of our device in comparison with other low-power CMOS voltage references reported in [9]–[13]. Our device is comparable to other circuits in power dissipation, PSRR, and chip area, and it is superior to others in TC and line sensitivity. Our circuit is therefore useful as a voltage reference for power-aware LSIs.

V. DISCUSSION

Regarding other applications, the output voltage of our circuit can be used as a monitor signal for the D2D process variation in MOSFET threshold voltage because the output voltage is equal to the 0-K threshold voltage of MOSFETs in an LSI chip.

$$\frac{\Delta I_P}{I_P} = \frac{\Delta \mu}{\mu} + \frac{\Delta C_{\text{OX}}}{C_{\text{OX}}} + \frac{\Delta \kappa}{\kappa}. \quad (20)$$

This output voltage can be used to compensate for the threshold voltage variation in LSI chips. For example, consider the application to a reference current source. The process variation of the current $I_P$ flowing in our circuit [see (14)] can be expressed as

$$\mu = 0.747 \text{ V}$$
$$\sigma = 0.007 \text{ V}$$

This way, the circuit can be used as an elementary circuit block for on-chip D2D process compensation systems, such as process and temperature compensated current [23].

VI. CONCLUSION

We developed an ultra-low power CMOS voltage reference consisting of subthreshold MOSFET circuits. The device generates two voltages having opposite TCs, i.e., a MOSFET threshold voltage and a multiple of the thermal voltage, and adds them to produce an output voltage with a zero TC. We
made a prototype chip, using a 0.35 μm standard CMOS process, and demonstrated its operation by measurements. The TC and line sensitivity of the output voltage were 7 ppm/°C and 20 ppm/V. The power dissipation was about 0.3 μW. The circuit will be useful as a voltage reference circuit for a power-aware LSIs such as mobile devices, implantable medical devices, and smart sensor networks.

As other applications, because the reference voltage changes with the process conditions of threshold voltage in each LSI chip, the circuit can be used as an elementary circuit block for on-chip process compensation systems. The reference voltage of the proposed circuit enables us to monitor the D2D process variations in each LSI chip.

**APPENDIX**

On condition that \( V_{\text{REF}} \ll kT \) and \( \eta T \ll kT \), the TC of \( V_{\text{REF}} \) in (10) can be rewritten as

\[
\frac{dV_{\text{REF}}}{dT} = -\kappa + \frac{\eta T}{q} \ln \left( \frac{6g\eta K_3 K_5 (V_{\text{REF}} - V_{\text{THD}}) + kT}{K_4 K_6 K_7 (\eta - 1) V_T} \right)
\]

\[
\times \ln \left( \frac{K_2}{K_1} \right)
\]

\[
+ \eta T \left( \frac{1}{V_{\text{REF}} - V_{\text{THD}} + kT} \left( \frac{dV_{\text{REF}}}{dT} + \kappa \right) - \frac{1}{T} \right)
\]

\[
= -\kappa + \frac{\eta T}{q} \ln \left( \frac{6g\eta K_3 K_5 kT}{K_4 K_6 K_7 (\eta - 1) V_T} \right) + \ln \left( \frac{K_2}{K_1} \right)
\]

\[
+ \eta T \left( \frac{dV_{\text{REF}}}{dT} + \kappa \right) - \eta \frac{V_T}{T}
\]

\[
= -\kappa + \frac{\eta T}{q} \ln \left( \frac{6g\eta K_3 K_5 kT}{K_4 K_6 K_7 (\eta - 1) V_T} \right) + \ln \left( \frac{K_2}{K_1} \right)
\]

\[
+ \frac{\eta T}{kT} \frac{dV_{\text{REF}}}{dT}
\]

\[
= -\kappa + \frac{\eta T}{q} \ln \left( \frac{6g\eta K_3 K_5 kT}{k (\eta - 1)} \right) + \ln \left( \frac{K_2}{K_1} \right).
\]

Therefore, (11) can be obtained.

**REFERENCES**


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